

# Electrochemical characterization of boron-doped nanocrystalline diamond electrodes for neural stimulation

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THE use of diamond for neural stimulation has been of interest, as the mechanical, chemical and biological stability of the material are advantageous [1, 2]. Electrochemically, it is advantageous that diamond electrodes have a wide potential window in which safe stimulation can be applied. However, as diamond naturally is an insulating material, a dopant must be employed in order to improve its electrical properties [1]. In this paper, the electrochemical properties of B-NCD electrodes are compared to those of smooth and porous TiN electrodes. The electrodes are compared using the electrode impedance magnitude ( $|Z|$ ), its charge injection capacity ( $Q_{inj}$ ), its cathodic charge storage capacity ( $CSC_c$ ) and its capacitance.

All coatings were applied to a semi-spherical monopolar Ti6Al4V substrate (surface area:  $0.06 \text{ cm}^2$ ). The TiN coatings were deposited using magnetron sputtering and had a thickness of  $\sim 4 \text{ }\mu\text{m}$ . B-NCD was grown using a pulsed microwave plasma enhanced chemical vapor deposition apparatus with linear antenna delivery system [3] operating at low pressures with a  $\text{CH}_4\text{-H}_2\text{-CO}_2$  chemistry with trimethylboron (TMB) as a boron dopant.

Electrochemical measurements on three B-NCD electrodes were compared to measurements on a smooth and a porous TiN electrode. Measurements were performed in phosphate buffered saline (PBS) at room temperature. EIS was performed using Solartron, Model 1294 in conjunction with 1260 Impedance/gain-phase Analyzer (Solartron Analytical, UK). The impedance spectrum was measured from 0.1 Hz – 100 kHz using a current of  $5.0 \text{ }\mu\text{A}$ . The electrolyte resistance was subtracted from the measured impedance. Voltage transient measurements (VTM) and cyclic voltammetry (CV) were performed using a VersaSTAT 3 potentiogalvanostat (Princeton applied research, USA). The water window potentials were established for the B-NCD electrodes, after which CV measurements were made at sweep rates of 0.05, 0.1, 0.5 and 1.0 V/s. For TiN -0.6 and 0.9 V vs. Ag/AgCl were used as water window potentials. The  $CSC_c$  was computed at 0.05 V/s [4]. VTM was performed using a biphasic cathodic-first current pulse (phase width: 0.2 ms) with a  $40 \text{ }\mu\text{s}$  interphase.  $Q_{inj}$  was reached when the electrode potential exceeded the water window potential. The electrode capacitance is computed using the CV and the VTM data [1].

Table 1 shows that the porous TiN electrode outperforms the smooth TiN and the B-NCD electrodes at all aspects. The B-NCD and smooth TiN electrodes show comparable values, especially when it comes to  $|Z|$ ,  $Q_{inj}$  and capacitance.  $Q_{inj}$  could not be determined for the porous TiN electrodes, due to machine limitations. The typical wide water window was found for B-NCD electrodes, from -1.7 to 1.4 V vs. Ag/AgCl [1].

The properties of the B-NCD electrodes are comparable to those described in literature [1] and in the same range as the properties of the smooth TiN electrode. However, the porous TiN electrode clearly outperforms both. So is there any future for B-NCD neural stimulation electrodes? We believe so. Nano-structures may be a means to increase the electrochemical surface area and thus further improve the electrochemical properties of the B-NCD electrodes. A diamond coating has been grown on a nanostructured polymer substrate before [5], but challenges remain depositing diamond on a porous metal substrate [6].

TABLE I.  $|Z|$ ,  $CSC_c$ ,  $Q_{inj}$  AND CAPACITANCE OF B-NCD, SMOOTH AND POROUS TiN ELECTRODES (MEAN $\pm$ STANDARD ERROR).

Electrode	EIS		CV		VTM	
	$ Z $ at 1 kHz ( $\Omega$ )	$ Z $ at 1 Hz ( $\Omega$ )	$CSC_c$ ( $\text{mC}/\text{cm}^2$ )	Capacitance ( $\mu\text{F}/\text{cm}^2$ )	$Q_{inj}$ ( $\mu\text{C}/\text{cm}^2$ )	Capacitance ( $\mu\text{F}/\text{cm}^2$ )
B-NCD	$212 \pm 12$	$(195 \pm 22) \cdot 10^3$	$5.1 \pm 0.64$	$40 \pm 6$	$26 \pm 1$	$8.2 \pm 0.1$
Smooth TiN	138	$92 \cdot 10^3$	0.14	51	27	$15.2 \pm 0.7$
Porous TiN	0	35	86	$23 \cdot 10^3$	-	$(1.9 \pm 0.09) \cdot 10^3$

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